



#### DUAL P-CHANNEL ENHANCEMENT MODE MOSFET

#### **Product Summary**

V <sub>(BR)DSS</sub>	R <sub>DS(ON)</sub>	Ι <sub>D</sub> T <sub>A</sub> = +25°C
-50V	6Ω @ V <sub>GS</sub> = -4 V	-160mA
-507	8Ω @ V <sub>GS</sub> = -2.5V	-120mA

#### Descriptions

This new generation MOSFET has been designed to minimize the on-state resistance ( $R_{DS(on)}$ ) and yet maintain superior switching performance, making it ideal for high efficiency power management applications.

#### **Applications**

- DC-DC Converters
- Power Management Functions
- Battery Operated Systems and Solid-State Relays





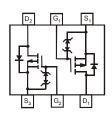
TOP VIEW

#### **Features and Benefits**

- Low On-Resistance
- ESD Protected Gate
- Low Input Capacitance
- Fast Switching Speed
- Lead-Free Finish; RoHS Compliant (Notes 1 & 2)
- Halogen and Antimony Free. "Green" Device (Note 3)
- Qualified to AEC-Q101 Standards for High Reliability

#### **Mechanical Data**

- Case: SOT563
- Case Material: Molded Plastic, "Green" Molding Compound. UL Flammability Classification Rating 94V-0
- Moisture Sensitivity: Level 1 per J-STD-020D
- Terminals: Finish Matte Tin annealed over Copper leadframe. Solderable per MIL-STD-202, Method 208 <sup>3</sup>
- Weight: 0.006 grams (approximate)



TOP VIEW Internal Schematic

#### Ordering Information (Note 4)

Part Number	Case	Packaging
DMP56D0UV -7	SOT563	3000/Tape & Reel
DMP56D0UV -13	SOT563	10000/Tape & Reel

SOT563

1. EU Directive 2002/95/EC (RoHS) & 2011/65/EU (RoHS 2) compliant. All applicable RoHS exemptions applied.

2. See http://www.diodes.com/quality/lead\_free.html for more information about Diodes Incorporated's definitions of Halogen- and Antimony-free, "Green" and Lead-free.

3. Halogen- and Antimony-free "Green" products are defined as those which contain <900ppm bromine, <900ppm chlorine (<1500ppm total Br + Cl) and <1000ppm antimony compounds.

4. For packaging details, go to our website at http://www.diodes.com/products/packages.html.

### **Marking Information**

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	KI	D3	Y	М	
Ъ					

KD3 = Product Type Marking Code YM = Date Code Marking Y = Year (ex: V = 2008) M = Month (ex: 9 = September)

Date Code Key

Notes:

Year	2008		2009	2010		2011	2012	2	2013	2014		2015
Code	V		W	Х		Y	Z		А	В		С
Month	Jan	Feb	Mar	Apr	Мау	Jun	Jul	Aug	Sep	Oct	Nov	Dec
Code	4	0	2	4	E	6	7	0	0	0	N	D



#### **Maximum Ratings** (@T<sub>A</sub> = +25°C, unless otherwise specified.)

Character	istic	Symbol	Value	Units
Drain-Source Voltage		V <sub>DSS</sub>	-50	V
Gate-Source Voltage	Continuous	V <sub>GSS</sub>	±8	V
Drain Current (Note 5)	Continuous	ID	-160	mA
Pulsed Drain Current (10µs pulse, d	uty cycle = 1%)	I <sub>DM</sub>	-700	mA

#### **Thermal Characteristics** (@T<sub>A</sub> = +25°C, unless otherwise specified.)

Characteristic	Symbol	Value	Units
Total Power Dissipation (Note 5)	PD	400	mW
Thermal Resistance, Junction to Ambient (Note 5)	$R_{ ext{ heta}JA}$	313	°C/W
Operating and Storage Temperature Range	T <sub>J</sub> , T <sub>STG</sub>	-55 to +150	°C

## Electrical Characteristics (@T<sub>A</sub> = +25°C, unless otherwise specified.)

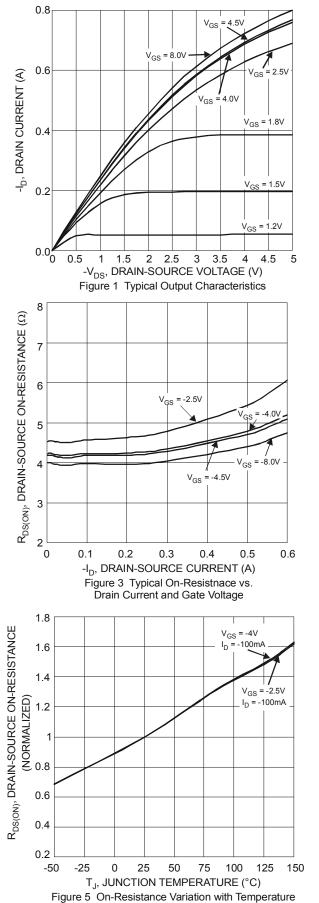
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Characteristic	Symbol	Min	Тур	Max	Unit	Test Condition
OFF CHARACTERISTICS (Note 6)			r			
Drain-Source Breakdown Voltage	BV <sub>DSS</sub>	-50			V	V <sub>GS</sub> = 0V, I <sub>D</sub> = -250µA
Zero Gate Voltage Drain Current	I <sub>DSS</sub>	_		-10	μA	V <sub>DS</sub> = -50V, V <sub>GS</sub> = 0V
Gate-Body Leakage	I <sub>GSS</sub>	_		±1	μA	$V_{GS} = \pm 8V, V_{DS} = 0V$
ON CHARACTERISTICS (Note 6)						
Gate Threshold Voltage	V <sub>GS(th)</sub>	-0.5	—	-1.2	V	$V_{DS} = V_{GS}, I_{D} = -250 \mu A$
Static Drain-Source On-Resistance	Б	_	4.6	6	0	V <sub>GS</sub> = -4V, I <sub>D</sub> = -100mA
Static Drain-Source On-Resistance	R <sub>DS (ON)</sub>	—	6.0	8	Ω	V <sub>GS</sub> = -2.5V, I <sub>D</sub> = -80mA
Forward Transfer Admittance	Y <sub>fs</sub>	100		_	mS	V <sub>DS</sub> = -5V, I <sub>D</sub> = -100mA
Diode Forward Voltage	V <sub>SD</sub>		—	-1.2	V	V <sub>GS</sub> = 0V, I <sub>S</sub> = -100mA
DYNAMIC CHARACTERISTICS (Note 7)						
Input Capacitance	Ciss		50.54	_	pF	
Output Capacitance	Coss		3.49	_	pF	V <sub>DS</sub> = -25V, V <sub>GS</sub> = 0V, f = 1.0MHz
Reverse Transfer Capacitance	C <sub>rss</sub>	_	2.42	_	pF	
Gate Resistance	R <sub>G</sub>	_	201		Ω	V <sub>DS</sub> = 0V, V <sub>GS</sub> = 0V, f = 1.0MHz
Total Gate Charge V <sub>GS</sub> = 4.5V	Qg	_	0.58	_	nC	(
Gate-Source Charge	Q <sub>gs</sub>	_	0.09		nC	$V_{GS} = -4V, V_{DS} = -25V,$
Gate-Drain Charge	Q <sub>gd</sub>		0.14		nC	I <sub>D</sub> = -100mA
Turn-On Delay Time	t <sub>D(on)</sub>		4.46		nS	
Turn-On Rise Time	tr	_	6.63		nS	V <sub>DD</sub> = -30V, I <sub>D</sub> = -0.27A, V <sub>GEN</sub> = -4V,
Turn-Off Delay Time	t <sub>D(off)</sub>	_	21.9		nS	$R_{GEN} = 6\Omega$
Turn-Off Fall Time	t <sub>f</sub>	_	15.0		nS	

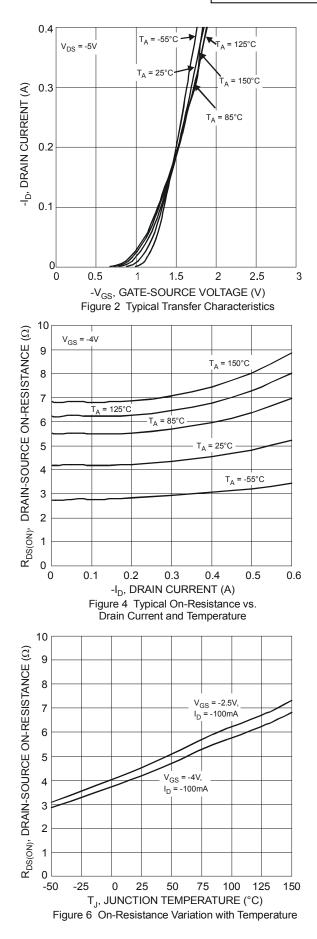
Notes:

Device mounted on FR-4 PC board, with minimum recommended pad layout, single sided.
Short duration pulse test used to minimize self-heating effect.
Guaranteed by design. Not subject to production testing.



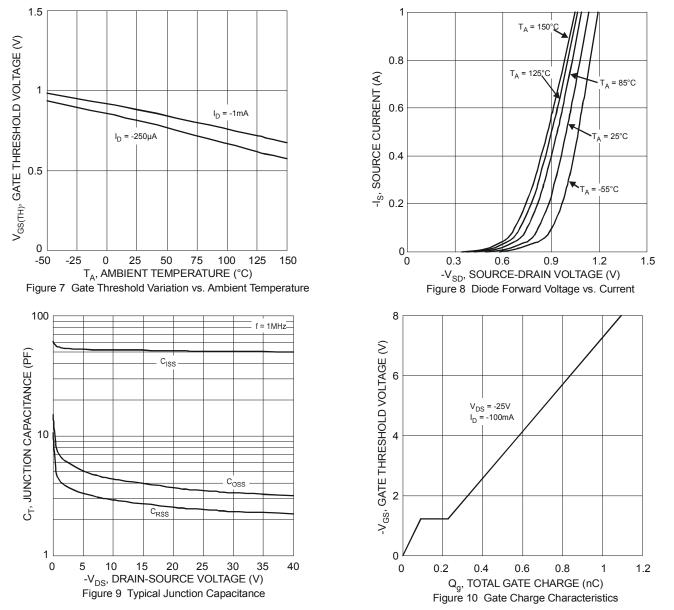




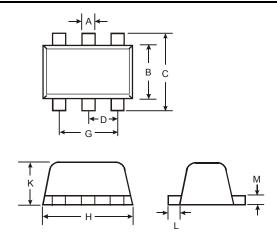




## DMP56D0UV



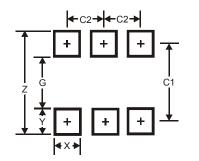
## **Package Outline Dimensions**



	SOT563					
Dim	Min	Max	Тур			
Α	0.15	0.30	0.20			
В	1.10	1.25	1.20			
С	1.55	1.70	1.60			
D	-	-	0.50			
G	0.90	1.10	1.00			
Η	1.50	1.70	1.60			
Κ	0.55	0.60	0.60			
L	0.10	0.30	0.20			
М	0.10	0.18	0.11			
All	Dimens	sions in	mm			



## Suggested Pad Layout



Value (in mm)
2.2
1.2
0.375
0.5
1.7
0.5

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